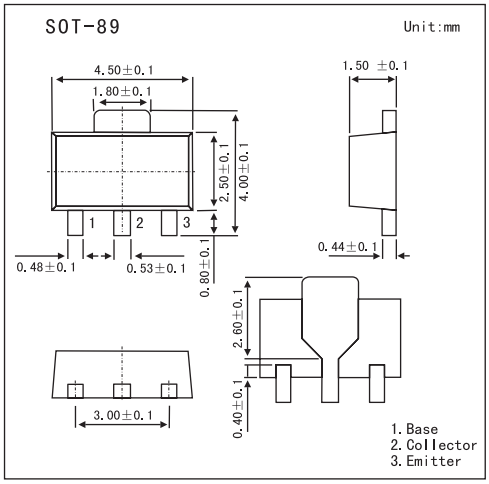
Medium power transistor

2SA1900



■ Features

- Low saturation voltage, typically $V_{CE(sat)}$ = ?0.15V at IC / I_B = ?500mA / ?50mA
- P_C=2W (on 40X40X0.7mm ceramic board)

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-emitter Voltage	V_{CEO}	-60	V
Collector-base Voltage	V_{CBO}	-50	V
Emitter-base Voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
		-2	A(Pulse) *1
Collector power dissipation	P_C	0.5	W
		2	W *2
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

*1 Single pulse Pw=20ms, Duty=1/2

*2 When mounted on a 40X40X0.7mm seramic board.

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltae	BV_{CBO}	I_C = -50□A	-60			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C = -1mA	-50			V
Emitter-base breakdown voltage	BV_{EBO}	I_E = -50□A	-5			V
Collector cutoff current	I_{CBO}	V_{CB} = -40V			-0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = -4V			-0.1	μA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C/I_B = -500mA/-50mA			-0.4	V
DC current transfer ratio	h_{FE}	V_{CE}/I_C = -3V/-0.5A	120		270	
Transition frequency	f_T	V_{CE} = -5V , I_E = 50mA , f=100MHz		150		MHz
Output Capacitance	C_{ob}	V_{CB} = -10V , I_E = 0A , f=1MHz		20		pF

■ Marking

Marking	ALQ